IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Prior Application: M. ISHIBASHI et al

Serial No. 09/090,942 Filed: June 5, 1998

Group Art Unit:

2851

Examiner:

P. Kim

For:

ELECTRON EXPOSURE APPARATUS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Washington, D.C. 20231

January 18, 2002

Sir:

In accordance with the duty of disclosure, the applicants inform the Examiner of the documents cited during prosecution of the parent application, USSN 09/090,942.

The applicants request the Examiner to initial and return a copy of the attached PTO-1449 form as an indication that the references have been considered.

Respectfully submitted,

Registration No. 32,846
Attorney for Applicant(s)

MATTINGLY, STANGER & MALUR, P.C. 1800 Diagonal Road, Suite 370 Alexandria, Virginia 22314 (703) 684-1120

Date: January 18, 2002

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